

Automotive-grade N-channel 80 V, 3.15 mΩ typ., 120 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

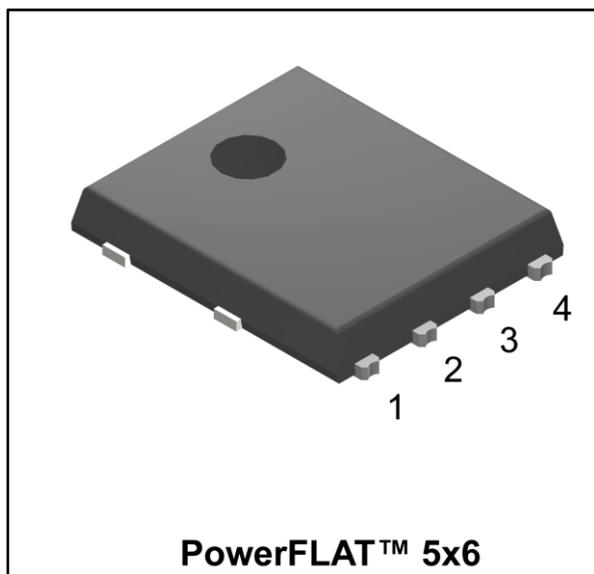


Figure 1: Internal schematic diagram

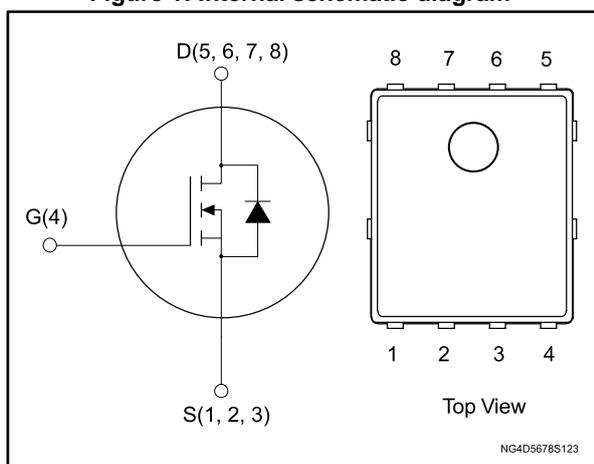


Table 1: Device summary

| Order code | Marking | Package | Packing |
|--------------|---------|----------------|---------------|
| STL135N8F7AG | 135N8F7 | PowerFLAT™ 5x6 | Tape and reel |

Features

| Order code | V _{DS} | R _{DS(on)} max. | I _D | P _{TOT} |
|--------------|-----------------|--------------------------|----------------|------------------|
| STL135N8F7AG | 80 V | 3.6 mΩ | 120 A | 135 W |

- Designed for automotive applications and AEC-Q101 qualified
- Among the lowest R_{DS(on)} on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness
- Wettable flank package

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

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1 Electrical ratings

Table 2: Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|-------------------|--|------------|------------------|
| V_{DS} | Drain-source voltage | 80 | V |
| V_{GS} | Gate-source voltage | ± 20 | V |
| $I_D^{(1)}$ | Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$ | 120 | A |
| | Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$ | 98 | |
| $I_{DM}^{(1)(2)}$ | Drain current (pulsed) | 480 | A |
| $I_D^{(3)}$ | Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$ | 26 | A |
| | Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$ | 19 | |
| $I_{DM}^{(2)(3)}$ | Drain current (pulsed) | 104 | A |
| $P_{TOT}^{(1)}$ | Total dissipation at $T_{case} = 25\text{ }^\circ\text{C}$ | 135 | W |
| $P_{TOT}^{(3)}$ | Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$ | 4.8 | W |
| $E_{AS}^{(4)}$ | Single pulse avalanche energy | 1.2 | J |
| T_{stg} | Storage temperature range | -55 to 175 | $^\circ\text{C}$ |
| T_j | Operating junction temperature range | | |

Notes:

- (1) This value is rated according to R_{thj-c}
- (2) Pulse width is limited by safe operating area
- (3) This value is rated according to $R_{thj-pcb}$
- (4) Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 13\text{ A}$, $V_{DD} = 50\text{ V}$

Table 3: Thermal data

| Symbol | Parameter | Value | Unit |
|---------------------|----------------------------------|-------|--------------------|
| $R_{thj-pcb}^{(1)}$ | Thermal resistance junction-pcb | 31.3 | $^\circ\text{C/W}$ |
| $R_{thj-case}$ | Thermal resistance junction-case | 1.1 | |

Notes:

- (1) When mounted on a 1-inch² FR-4 board, 2oz Cu, $t < 10\text{ s}$

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 4: Static

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------------------|---|------|------|------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | 80 | | | V |
| I_{DSS} | Zero gate voltage drain current | $V_{GS} = 0\text{ V}$, $V_{DS} = 80\text{ V}$ | | | 1 | μA |
| | | $V_{GS} = 0\text{ V}$, $V_{DS} = 80\text{ V}$, $T_j = 125\text{ °C}^{(1)}$ | | | 10 | |
| I_{GSS} | Gate-body leakage current | $V_{DS} = 0\text{ V}$, $V_{GS} = 20\text{ V}$ | | | 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2.5 | | 4.5 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}$, $I_D = 13\text{ A}$ | | 3.15 | 3.6 | m Ω |

Notes:

⁽¹⁾Defined by design, not subject to production test

Table 5: Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|--|------|------|------|---------------|
| C_{iss} | Input capacitance | $V_{DS} = 40\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$ | - | 6800 | - | μF |
| C_{oss} | Output capacitance | | - | 1350 | - | |
| C_{rss} | Reverse transfer capacitance | | - | 95 | - | |
| Q_g | Total gate charge | $V_{DD} = 40\text{ V}$, $I_D = 26\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 14: "Test circuit for gate charge behavior") | - | 103 | - | nC |
| Q_{gs} | Gate-source charge | | - | 35 | - | |
| Q_{gd} | Gate-drain charge | | - | 28 | - | |

Table 6: Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|---|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 40\text{ V}$, $I_D = 13\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 13: "Test circuit for resistive load switching times" and Figure 18: "Switching time waveform") | - | 30 | - | ns |
| t_r | Rise time | | - | 28 | - | |
| $t_{d(off)}$ | Turn-off delay time | | - | 73 | - | |
| t_f | Fall time | | - | 30 | - | |

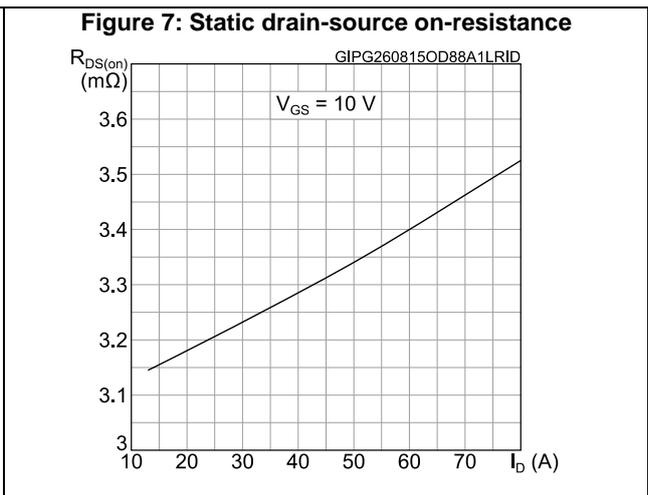
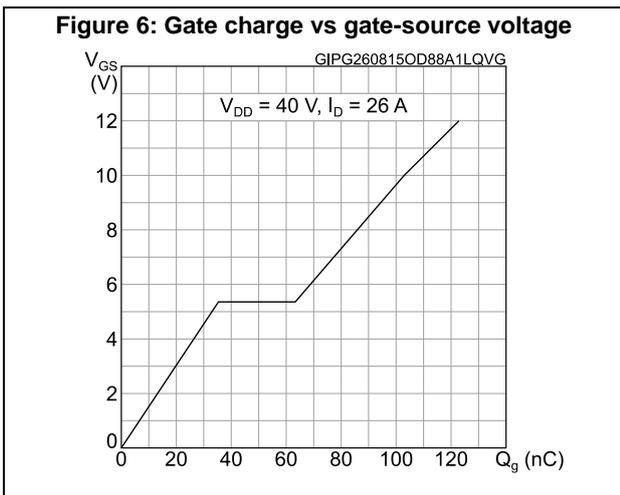
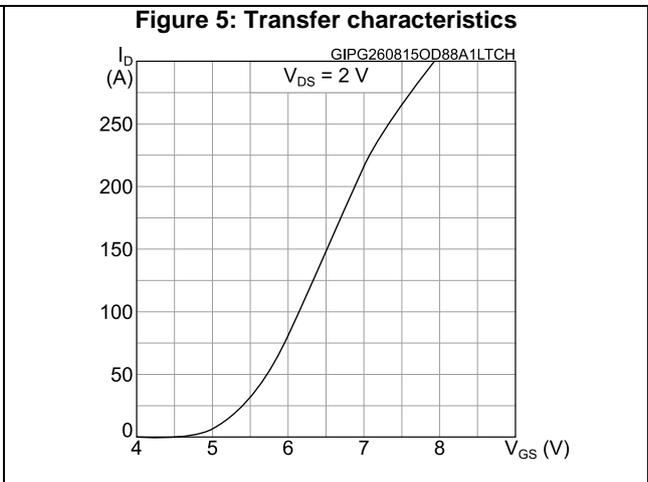
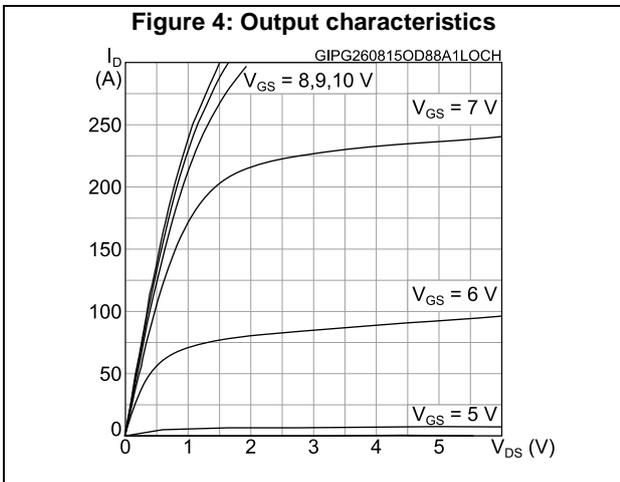
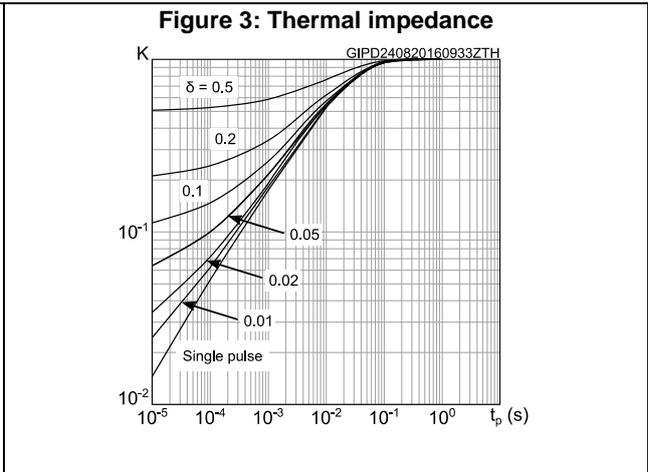
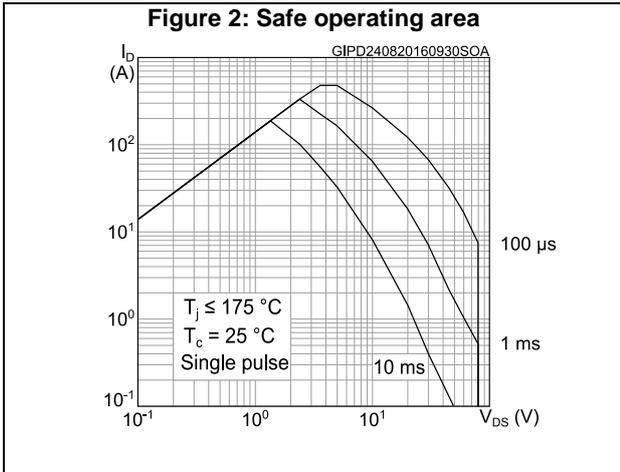
Table 7: Source-drain diode

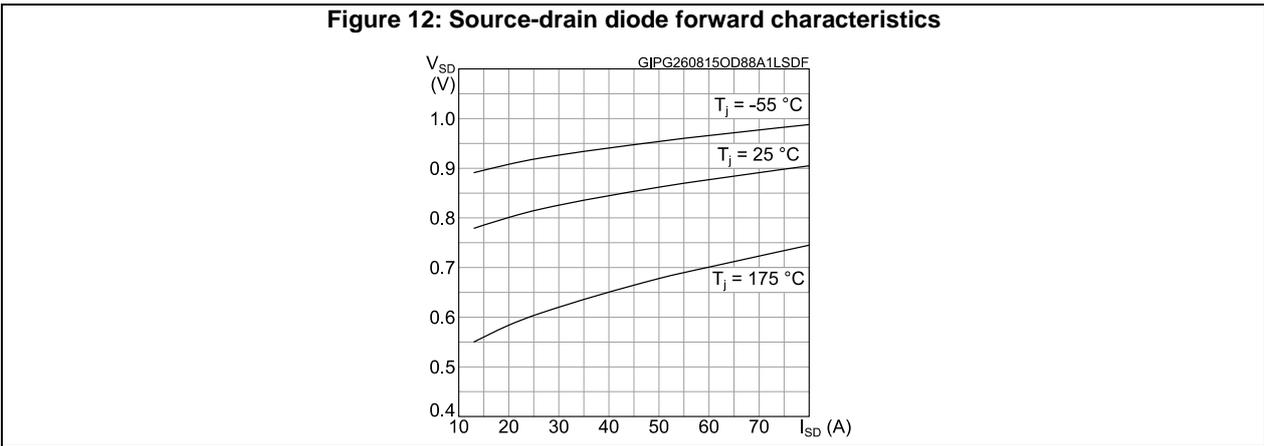
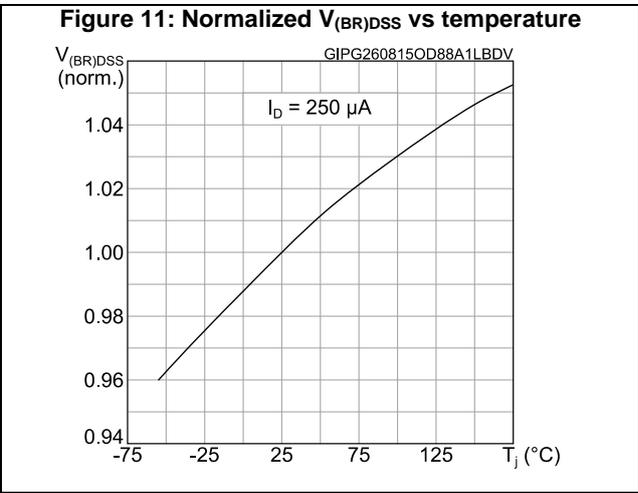
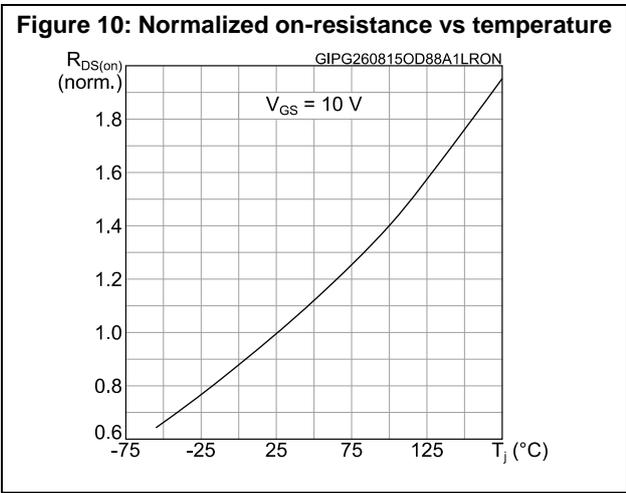
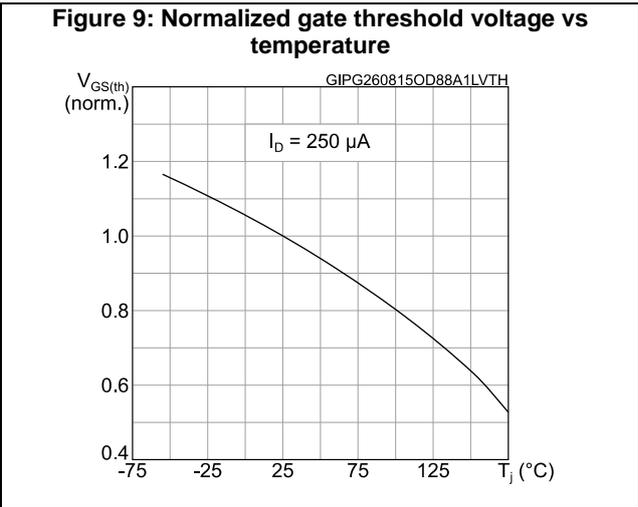
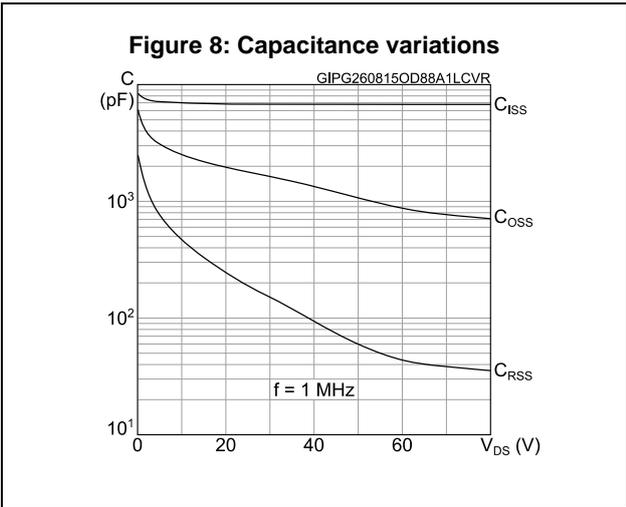
| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|--|------|------|------|------|
| I_{SD} | Source-drain current | | - | | 26 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 104 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $V_{GS} = 0\text{ V}$, $I_{SD} = 26\text{ A}$ | - | | 1.2 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 26\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 64\text{ V}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times") | - | 47 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 66 | | nC |
| I_{RRM} | Reverse recovery current | | - | 2.8 | | A |

Notes:

- (1) Pulse width is limited by safe operating area
(2) Pulse test: pulse duration = 300 μs , duty cycle 1.5%

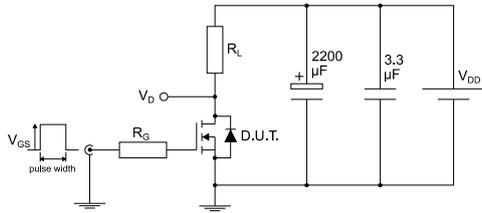
2.1 Electrical characteristics (curves)





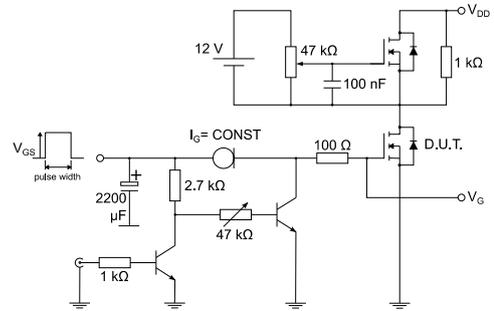
3 Test circuits

Figure 13: Test circuit for resistive load switching times



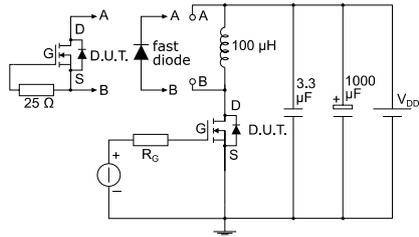
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Figure 14: Test circuit for gate charge behavior



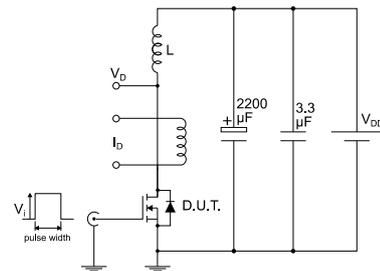
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Figure 15: Test circuit for inductive load switching and diode recovery times



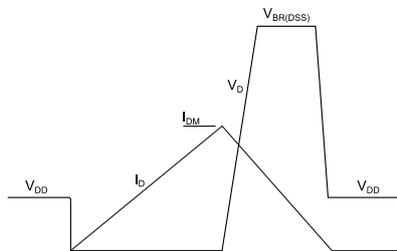
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Figure 16: Unclamped inductive load test circuit



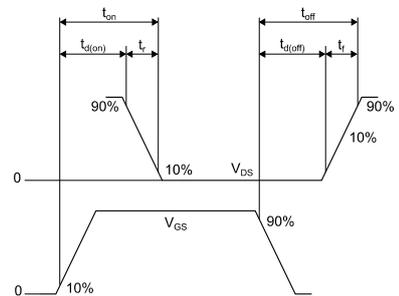
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Figure 17: Unclamped inductive waveform



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Figure 18: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 5x6 WF type C package information

Figure 19: PowerFLAT™ 5x6 WF type C package outline

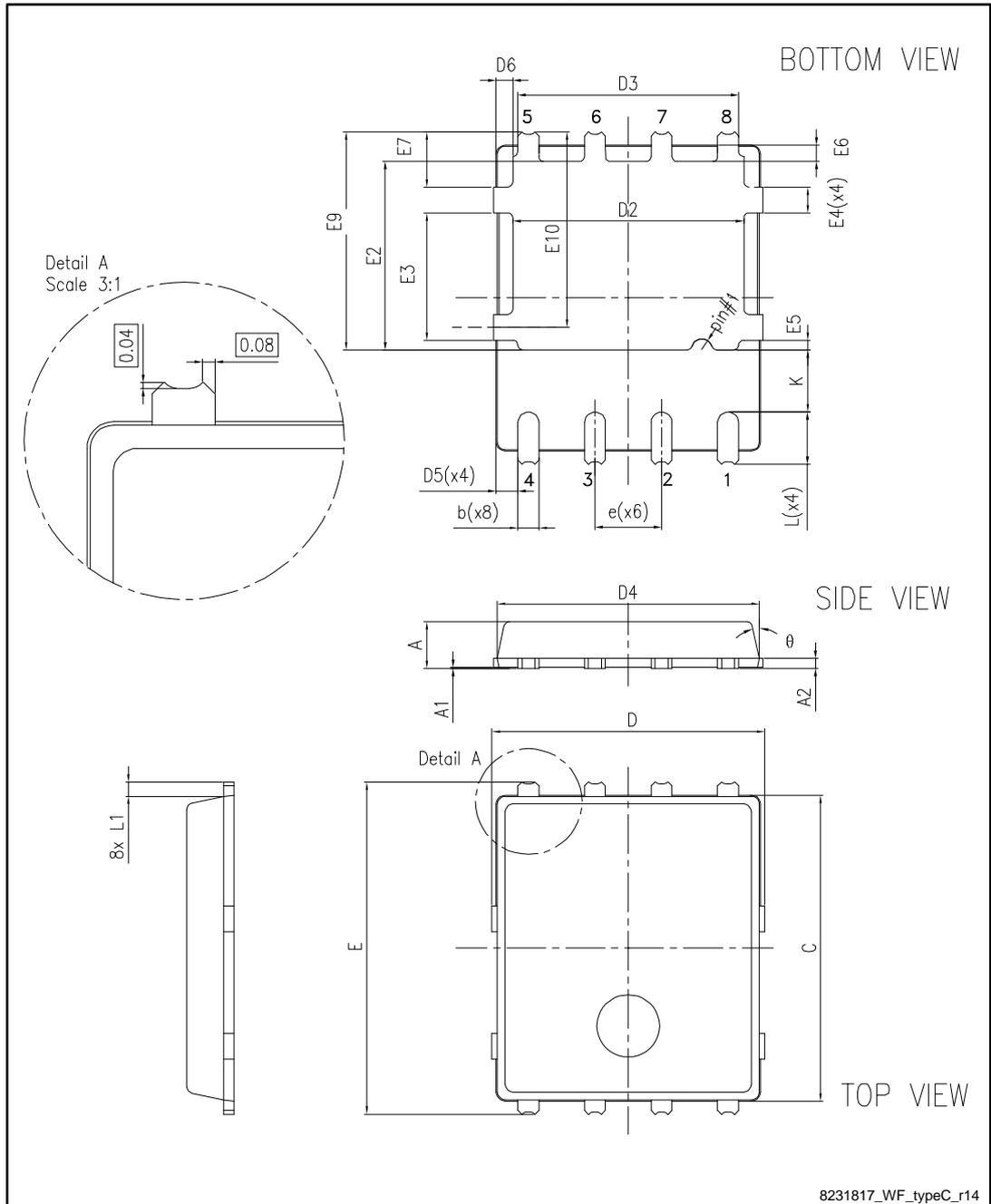
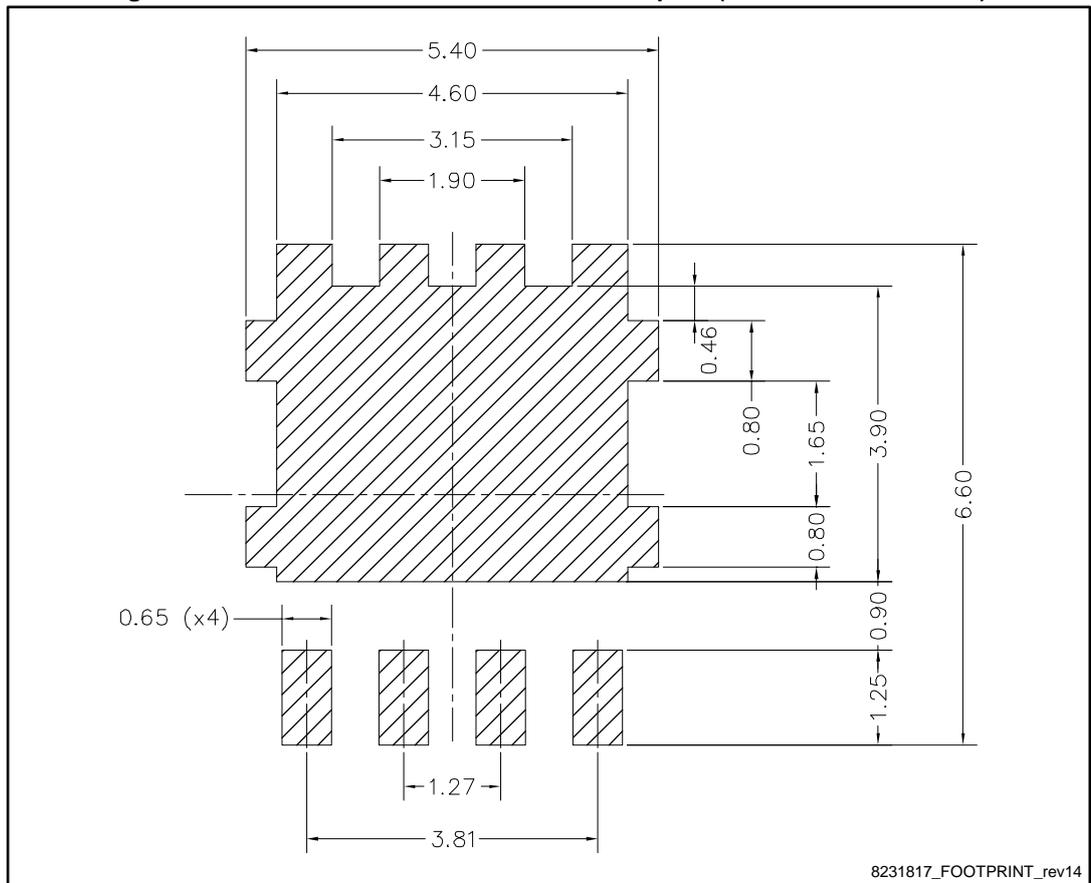


Table 8: PowerFLAT™ 5x6 WF type C mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 0.80 | | 1.00 |
| A1 | 0.02 | | 0.05 |
| A2 | | 0.25 | |
| b | 0.30 | | 0.50 |
| C | 5.80 | 6.00 | 6.10 |
| D | 5.00 | 5.20 | 5.40 |
| D2 | 4.15 | | 4.45 |
| D3 | 4.05 | 4.20 | 4.35 |
| D4 | 4.80 | 5.00 | 5.10 |
| D5 | 0.25 | 0.40 | 0.55 |
| D6 | 0.15 | 0.30 | 0.45 |
| e | | 1.27 | |
| E | 6.20 | 6.40 | 6.60 |
| E2 | 3.50 | | 3.70 |
| E3 | 2.35 | | 2.55 |
| E4 | 0.40 | | 0.60 |
| E5 | 0.08 | | 0.28 |
| E6 | 0.20 | 0.325 | 0.45 |
| E7 | 0.85 | 1.00 | 1.15 |
| E9 | 4.00 | 4.20 | 4.40 |
| E10 | 3.55 | 3.70 | 3.85 |
| K | 1.05 | | 1.35 |
| L | 0.90 | 1.00 | 1.10 |
| L1 | 0.175 | 0.275 | 0.375 |
| θ | 0° | | 12° |

Figure 20: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 WF packing information

Figure 21: PowerFLAT™ 5x6 WF tape (dimensions are in mm)

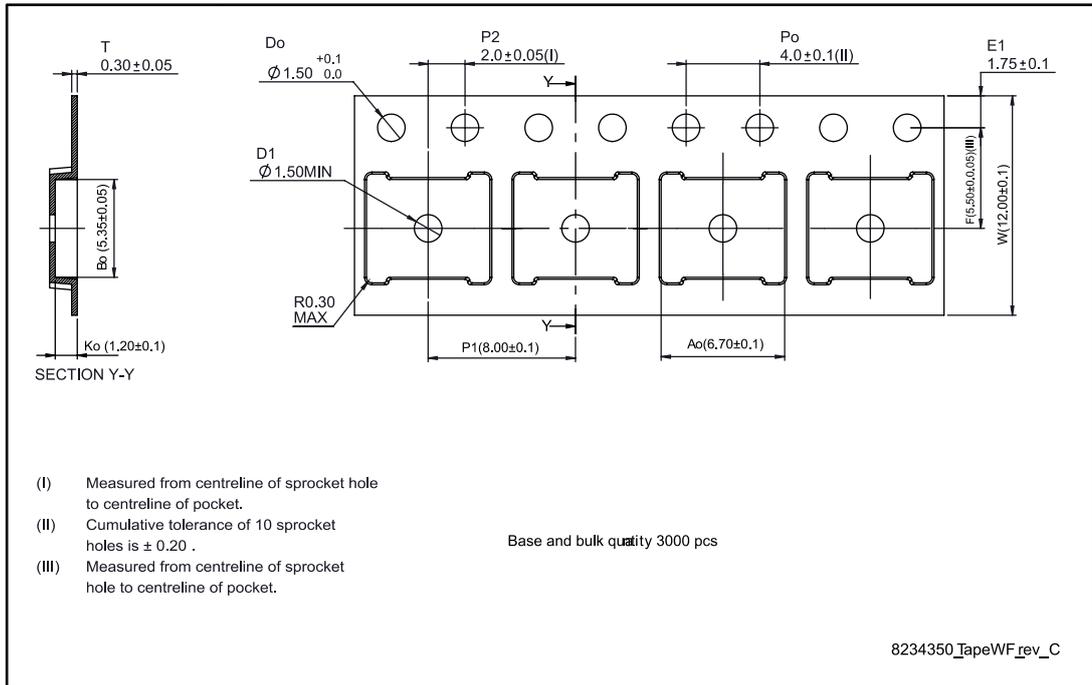


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape

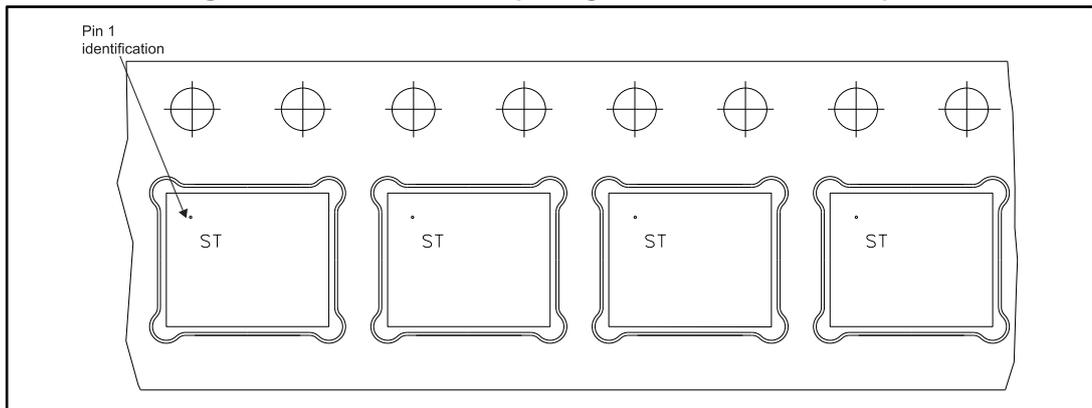
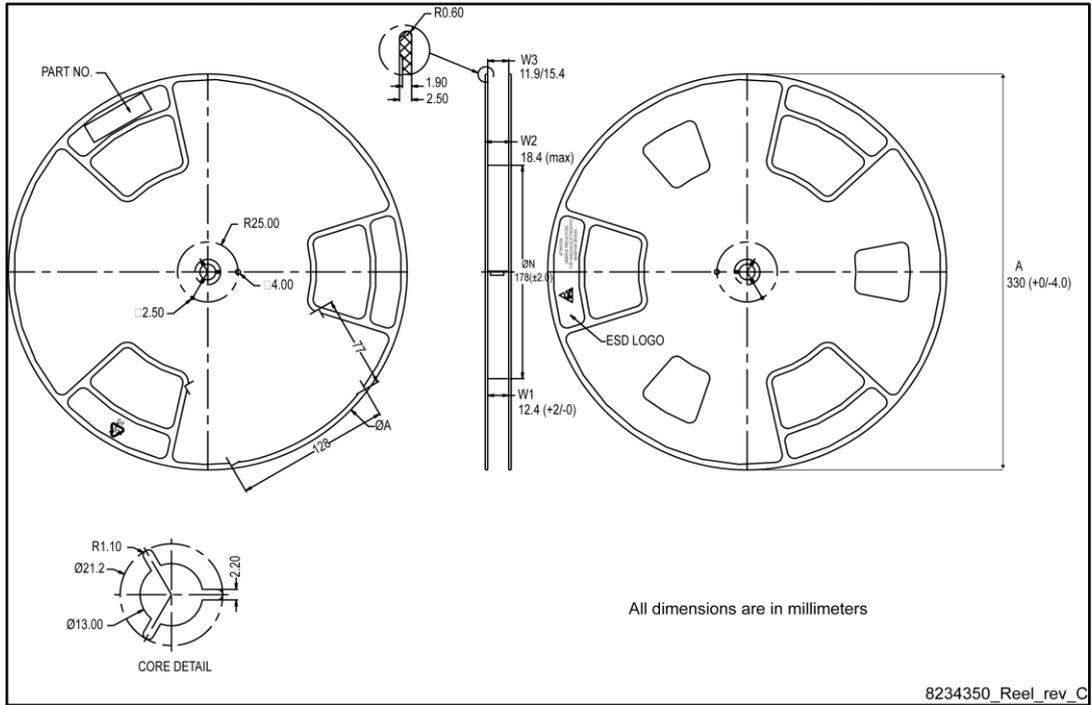


Figure 23: PowerFLAT™ 5x6 reel (dimensions are in mm)



5 Revision history

Table 9: Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 07-Sep-2015 | 1 | First release. |
| 15-Sep-2015 | 2 | Minor text edits. On cover page: - updated Title and Features. |
| 26-Jan-2016 | 3 | Updated <i>Table 2: "Absolute maximum ratings"</i> and <i>Section 4.1: "PowerFLAT™ 5x6 WF type C package information"</i> . |
| 16-Sep-2016 | 4 | Updated the silhouette, the title and the features in cover page. Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Figure 2: "Safe operating area"</i> and <i>Figure 3: "Thermal impedance"</i> . Minor text changes. |

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